PD-97198

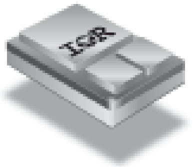
International
IOR Rectifier

RADIATION HARDENED POWER MOSFET SURFACE-MOUNT (SMD-0.5)

IRHNJ67C30
600V, N-CHANNEL
R6 TECHNOLOGY

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D
IRHNJ67C30	100K Rads (Si)	2.9Ω	3.4A
IRHNJ63C30	300K Rads (Si)	2.9Ω	3.4A



SMD-0.5

International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm^2). Their combination of very low $R_{DS(on)}$ and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low $R_{DS(on)}$
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I_D @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	3.4	A
I_D @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	2.2	
I_{DM}	Pulsed Drain Current ①	13.6	
P_D @ T_C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	76	mJ
I_{AR}	Avalanche Current ①	3.4	A
E_{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	9.2	V/ns
T_J T_{STG}	Operating Junction Storage Temperature Range	-55 to 150	°C
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	1.0 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	—	0.47	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	2.9	Ω	V_{GS} = 12V, I_D = 2.2A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
g_{fs}	Forward Transconductance	3.4	—	—	S (℧)	V_{DS} = 15V, I_{DS} = 2.2A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V_{DS} = 480V ,V_{GS}=0V
		—	—	25		V_{DS} = 480V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	44	nC	V_{GS} = 12V, I_D = 3.4A V_{DS} = 300V
Q_{gs}	Gate-to-Source Charge	—	—	14		
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	10		
$t_{d(on)}$	Turn-On Delay Time	—	—	17	ns	V_{DD} = 300V, I_D = 3.4A, V_{GS} = 12V, R_G = 7.5Ω
t_r	Rise Time	—	—	9.3		
$t_{d(off)}$	Turn-Off Delay Time	—	—	33		
t_f	Fall Time	—	—	17		
$L_S + L_D$	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C_{iss}	Input Capacitance	—	1222	—	pF	V_{GS} = 0V, V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	—	80	—		
C_{rss}	Reverse Transfer Capacitance	—	1.9	—		
R_g	Internal Gate Resistance	—	1.5	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.4	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	13.6		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_j = 25°C, I_S = 3.4A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	—	741	ns	T_j = 25°C, I_F = 3.4A, di/dt ≤ 100A/μs V_{DD} ≤ 50V ④
Q_{RR}	Reverse Recovery Charge	—	—	2.1	μC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	1.67	°C/W	

For footnotes refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si)		Units	Test Conditions
		Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	—	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0		$V_{GS} = V_{DS}$, I_D = 1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	-100		V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	—	10	µA	V_{DS}= 480V, V_{GS}= 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	2.9	Ω	V_{GS} = 12V, I_D = 2.2A
V_{SD}	Diode Forward Voltage ④	—	1.0	V	V_{GS} = 0V, I_D = 3.4A

Part numbers IRHNJ67C30 and IRHNJ63C30

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET	Energy	Range	VDS (V)			
	(MeV/(mg/cm^2))	(MeV)	(µm)	@VGS = 0V	@VGS = -4V	@VGS = -12V	@VGS = - 20V
Kr	32.4	679	83.3	600	600	600	600
Xe	56.2	1060	83.5	600	600	600	-
Au	89.5	1555	84	600	600	-	-

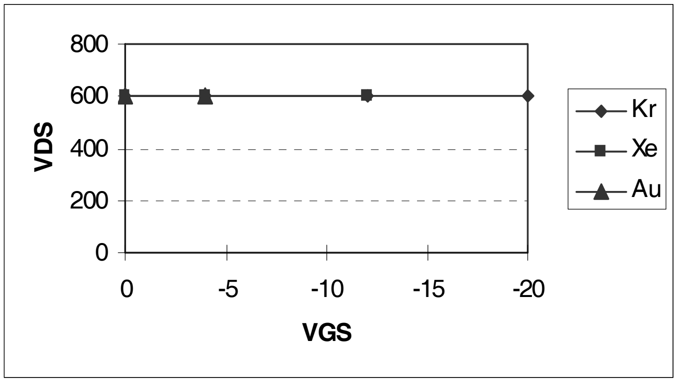


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

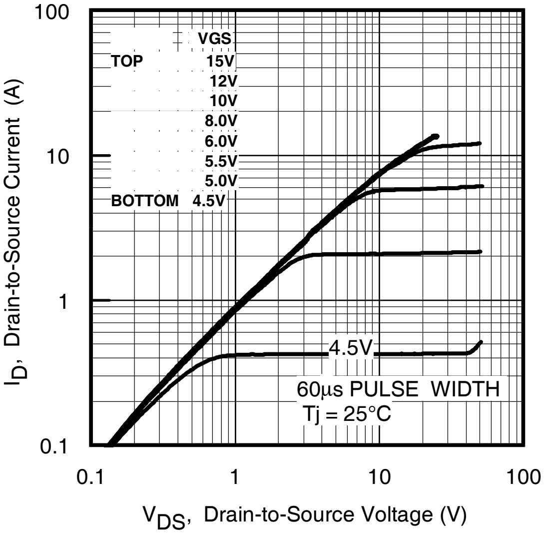


Fig 1. Typical Output Characteristics

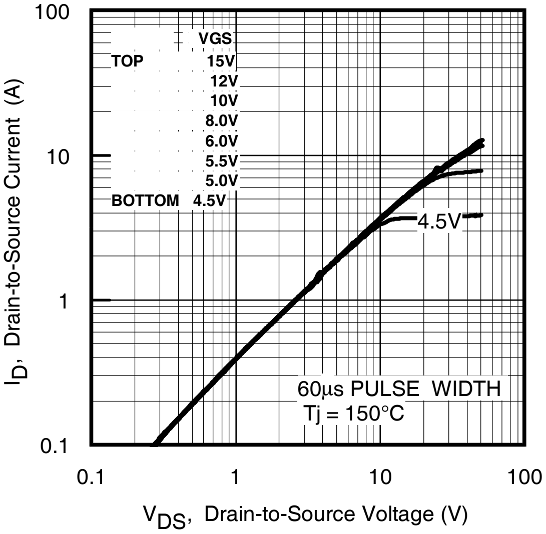


Fig 2. Typical Output Characteristics

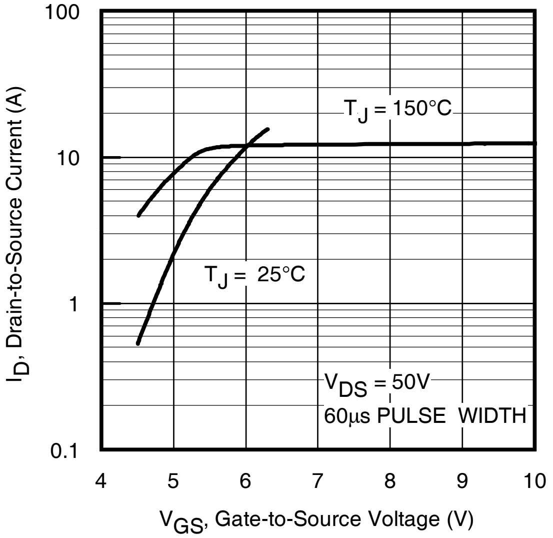


Fig 3. Typical Transfer Characteristics

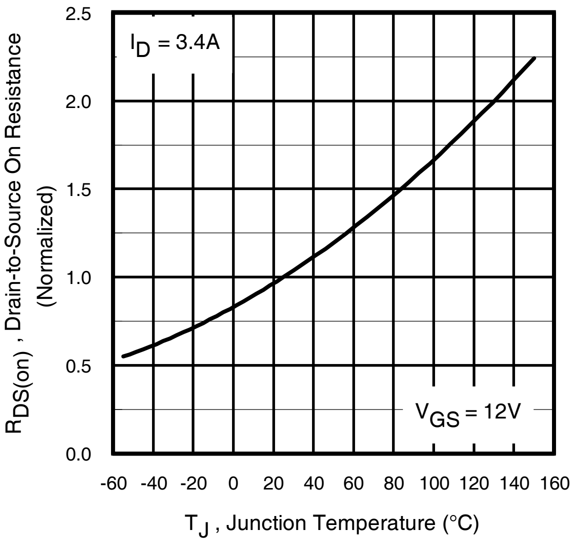


Fig 4. Normalized On-Resistance
Vs. Temperature

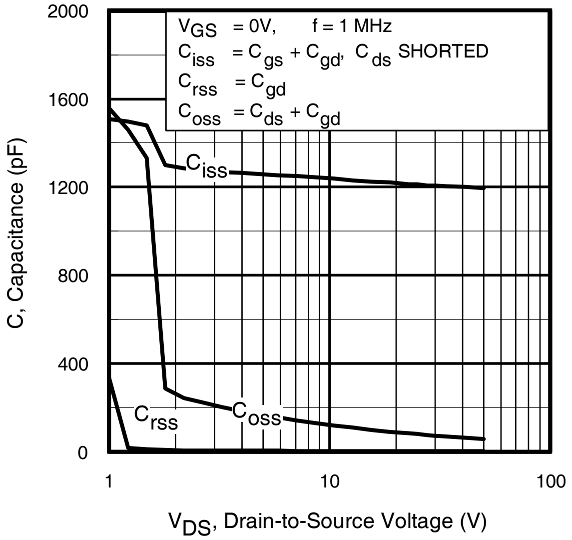


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

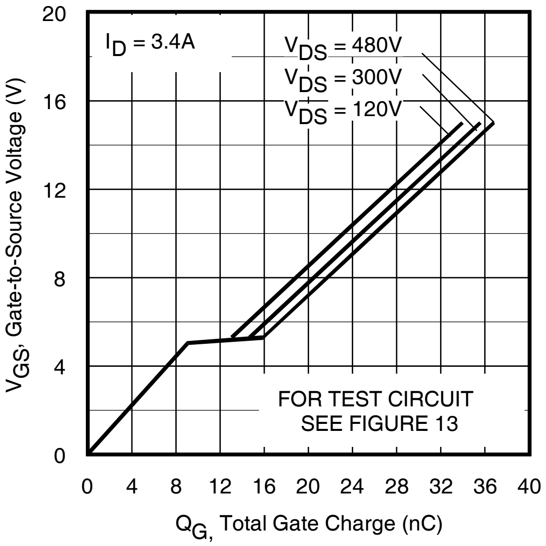


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

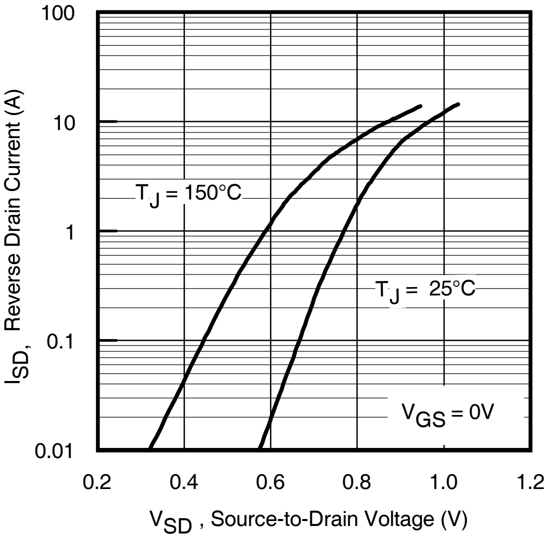


Fig 7. Typical Source-Drain Diode Forward Voltage

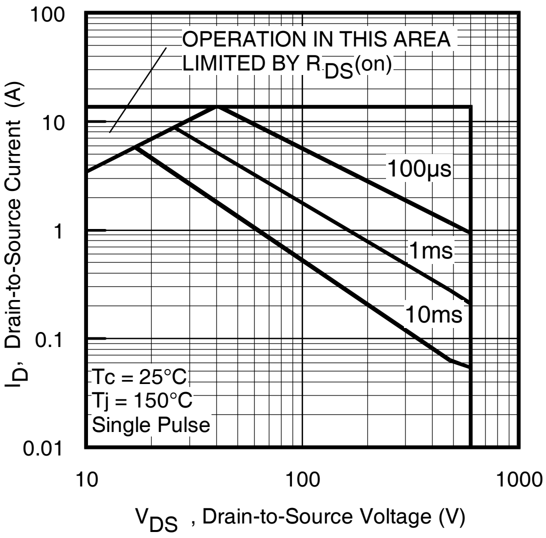


Fig 8. Maximum Safe Operating Area

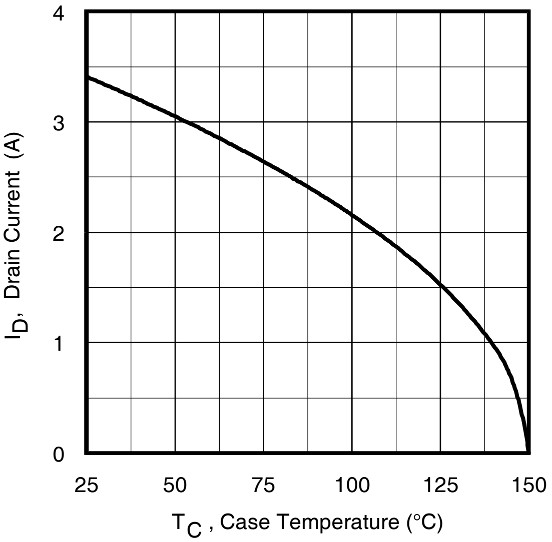


Fig 9. Maximum Drain Current Vs. Case Temperature

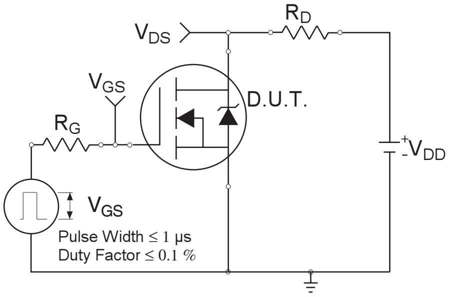


Fig 10a. Switching Time Test Circuit

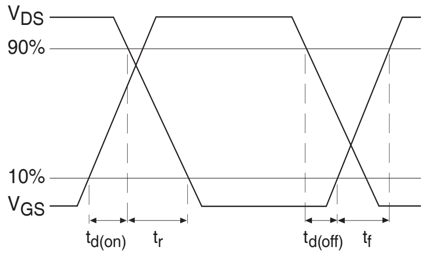


Fig 10b. Switching Time Waveforms

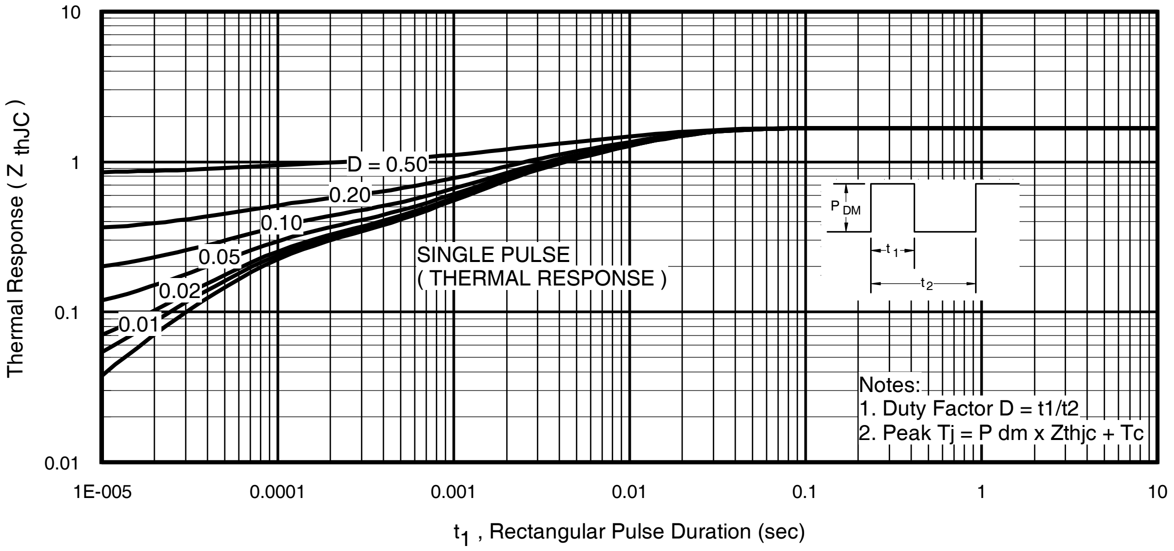


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

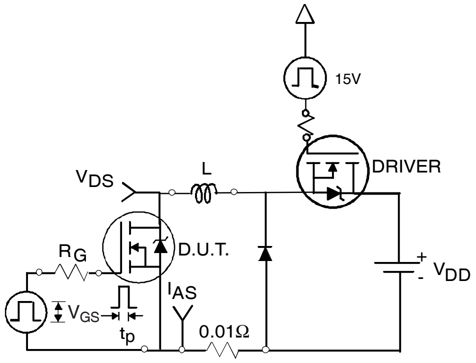


Fig 12a. Unclamped Inductive Test Circuit

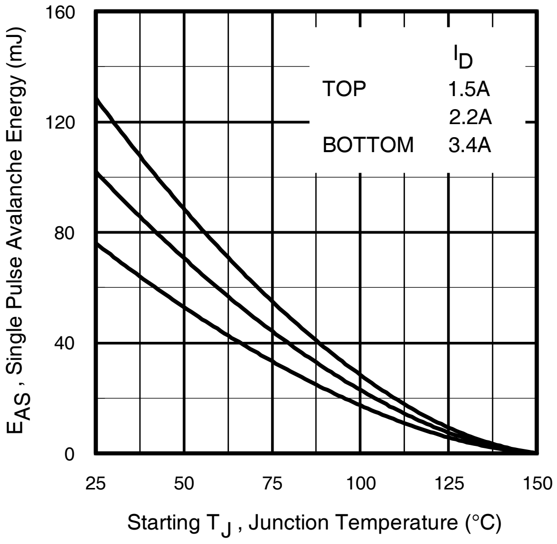


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

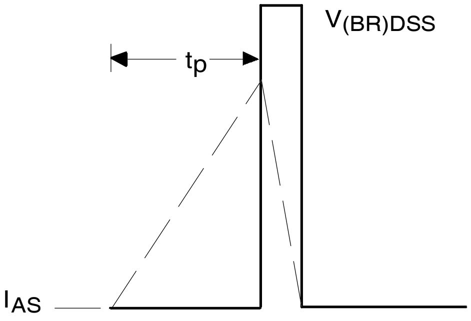


Fig 12b. Unclamped Inductive Waveforms

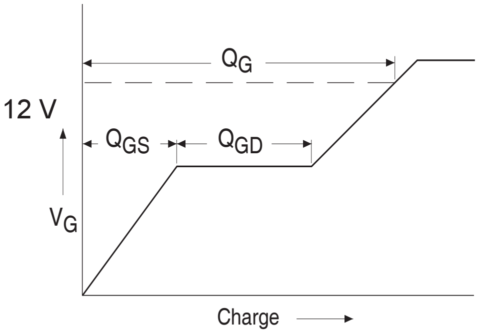


Fig 13a. Basic Gate Charge Waveform

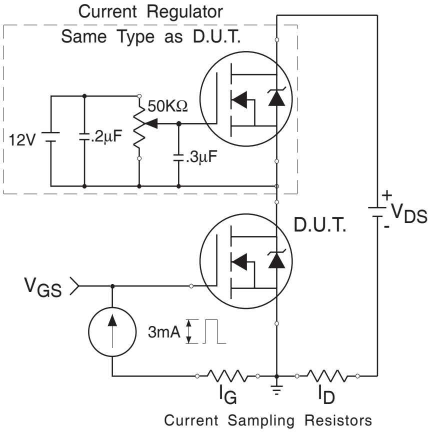


Fig 13b. Gate Charge Test Circuit

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 50V, starting T_J = 25°C, L= 13 mH Peak I_L = 3.4A, V_{GS} = 12V

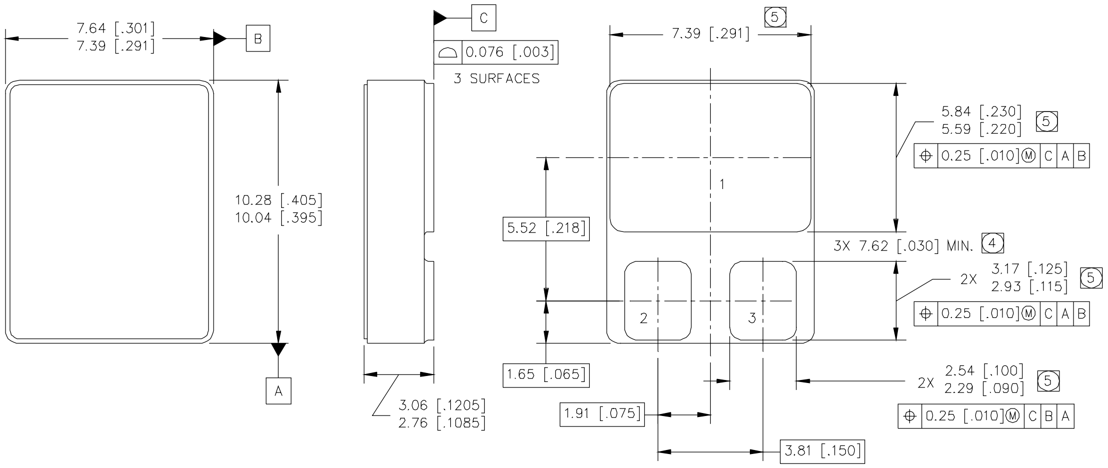
③ $I_{SD} \leq 3.4A$, $di/dt \leq 628A/\mu s$, $V_{DD} \leq 600V$, $T_J \leq 150°C$

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

⑤ **Total Dose Irradiation with V_{GS} Bias.** 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

⑥ **Total Dose Irradiation with V_{DS} Bias.** 480 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — SMD-0.5



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

④ DIMENSION INCLUDES METALLIZATION FLASH.

⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

1 = DRAIN
2 = GATE
3 = SOURCE

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.

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